

**Amendments to the Specification:**

Please replace paragraph 32 on page 17 with the following paragraph:

Another photoresist layer 532 may subsequently be formed having an opening 539 through which a deep source/drain implant may be performed to form deeply doped source/drain regions 306. The deep source/drain implant may include implanting an n-type dopant 535 at a dose and energy higher than that for the tip implant. For example, the dopant may comprise As implanted at a dose of about 8.0e15/cm<sup>2</sup> and an energy of about 50keV. The thick spacers 312 protect the source/drain extensions [[529]]526 beneath thick spacers 312 from being exposed to the deep source/drain implant, thus resulting in doped source/drain tips 537 and deeply doped source/drain regions 306. The source/drain tips 537 are merely the remnants of the source/drain extensions 526 and comprise the same lightly doped n-type material. In one embodiment of the invention, the deep regions 306 are formed to a concentration of between 1x10<sup>19</sup>/cm<sup>3</sup> - 5x10<sup>20</sup>/cm<sup>3</sup> and a depth of approximately 300Å to 2500Å. The deeply doped source/drain regions 306 and the polysilicon gate electrode 310 are exposed to the deep source/drain implant, thus deeply doping the polysilicon gate electrode 310.